

Rev. 04/03

Docket No. ELM-2 Cont. 4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/672,961 Confirmation No.: 9439

Filed : September 26, 2003

For : THREE DIMENSIONAL STRUCTURE

INTEGRATED CIRCUITS (AS AMENDED)

Group Art Unit : 2811

Examiner : Not yet assigned

New York, New York August 11, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information

Disclosure Statement in the above-identified application.

This Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. Hoh Registration No. 51,176

Agent for Applicants

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I hereby certify that time Correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope Addressed to: Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450 on

# ELM-2 Cont. 4

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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P.O. Box 1450

Alexandrian, Virginia 22313-1450

# INFORMATION DISCLOSURE STATEMENT

#### Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

# **U.S.** Patents

Fujii et al.	Re. 34,893	04/04/95
Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78
Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79

1		00/01/05
Hoeberechts	4,251,909	02/24/81
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
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Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
Takagi et al.	4,539,068	09/03/85
Reid et al.	4,585,991	04/29/86
Yasumoto et al.	4,612,083	09/16/86
Belanger et al.	4,617,160	10/14/86
Shimizu et al.	4,618,397	10/21/86
Schmitz		10/21/86
	4,618,763	
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
Hatada	4,693,770	09/15/87
Maeda et al.	4,702,336	10/27/87
Seibert et al.	4,702,936	10/27/87
Go	4,706,166	11/10/87
Stevenson	4,721,938	01/26/88
Reid	4,761,681	08/02/88
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Freeman	4,810,673	03/07/89
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Borel et al.	4,940,916	07/10/90
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Vranish et al.	4,950,987	08/21/90
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Rokos	4,954,865	09/04/90
Shinomiya	4,957,882	09/18/90
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Mauger	4,966,663	10/30/90
Leedy	4,994,735	02/19/91
	5,008,619	04/16/91
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Leedy	5,034,685	07/23/91
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Leedy	5,103,557	04/14/92
Mauger	5,110,373	05/05/92
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Roy	5,132,244	07/21/92
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	-,,,,	02,22,32

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Zimmerman	5,203,731	04/20/93
Leedy	5,205,731	07/06/93
<del>-</del>		08/17/93
Bower et al.	5,236,118	* *
Bureau et al.	5,262,351	11/16/93
Bertin et al.	5,270,261	12/14/93
Sanders	5,273,940	12/28/93
Tuckerman	5,274,270	12/28/93
Chebi et al.	5,279,865	01/18/94
Nakanishi et al.	5,284,796	02/08/94
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Wojnarowski	5,324,687	06/28/94
Leedy	5,354,695	10/11/94
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	5,420,458	05/30/95
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Finnila	5,426,072	06/20/95
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Leedy	5,571,741	11/05/96
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Ray	5,831,280	11/03/98
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Leedy	5,840,593	11/24/98
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Sweatt et al.	5,870,176	02/09/99
Davidson	5,880,010	03/09/99
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Leedy	6,133,640	10/17/00
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Lin	6,261,728 B1	07/17/01
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EPO	EP 0 731 525	09/1996
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"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).

Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of  $N_2$ -SiH $_4$  /A $_r$  and  $N_2$ -SiH $_4$ /He," Journal of the Electrochemical Society, Vol. 132, No. 7, pp. 1763-1766, (July 1985).

Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium, "pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be:

(1) fully considered by the Patent and Trademark Office

during the examination of this application; and (2) printed

on any patent which may issue on this application.

Applicant requests that a copy of Form PTO-1449, as

considered and initialized by the Examiner, be returned with

the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

I hereby certify that this '
Correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope

Addressed to:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450 on

Claire J. Saistik van Goodman

Signature of Person Signing

Philip R. Pol

Registration No. 51,176

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM-2 Cont. 4	APPLICATION NO. 10/672,961
••	NFORMATION DISCLOSURE	APPLICANT Glenn J. Leedy	CONFIRMATION NO. 9439
	STATEMENT BY APPLICANT	FILING DATE September 26, 2003	GROUP 2811

U.S. PATENT DOCUMENTS

EXAMINE R	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF
INITIAL		04/04/05	Full of all	257	419	APPROPRIATE
	Re. 34,893	04/04/95	Fujii et al.	<del>                                     </del>		
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
	4,693,770	09/15/87	Hatada	156	151	

**EXAMINER** 

FORM PTO-1449 U.S. DEPARTMENT OF COMME PATENT AND TRADEMARK OF			ATTY. DOO ELM-2 Con		APPLICATION NO. 10/672,961	
	INFORMATION DISCLOSURE STATEMENT BY APPLICANT			T eedy	CONFIRMATION NO. 9439	
			FILING DA September		GROUP 2811	
4,702,	336 10/27/8	7 Maeda et al.	180	197		
4,702,			427	583		
4,706,		7 Go	361	403		
4,721,9		8 Stevenson	338	4		
4,761,0		8 Reid	357	68		
4,784,			156	647		
4,810,6			438	386		
4,825,2		9 Mattox et al.	257	639		
4,857,4	181 08/15/8	9 Tam et al.	438	619		
4,924,	589 05/15/9		438	6		
4,940,9	916 07/10/9	0 Borel et al.	313	306		
Re B14	1,940,916 11/26/9	6 Borel et al.	315	306		
4,950,9	987 08/21/9	<u> </u>	324	207.23		
4,952,4	146 08/18/9	0 Lee et al.	428	220		
4,954,8	365 09/04/9	0 Rokos	257	378		
4,957,8	382 09/18/9	0 Shinomiya	438	65		
4,965,4	10/23/9	0 Young et al.	200	83 N		
4,966,6	663 10/30/9		205	656		
4,994,7	'35 02/19/9		324	158		
5,008,6	619 04/16/9	1 Keogh et al.	324	207.17		
5,010,0	04/23/9	1 Allen et al.	438	659		
5,020,2	219 06/04/9	1 Leedy	29	846		
5,034,6			324	158 F		
5,070,0	026 12/03/9	1 Greenwald et al.	437	3		
5,071,5	510 12/10/9	1 Findler et al.	156	647		
5,098,8	365 03/24/9	2 Machado et al.	438	788		
5,103,5	557 04/14/9	2 Leedy	29	832		
5,110,3	373 05/05/9	2 Mauger	148	33.2		
5,111,2	278 05/05/9	2 Eichelberger	357	75		
5,116,7	777 05/26/9	2 Chan et al.	438	234		
5,130,8	94 07/14/9	2 Miller	361	393		
5,132,2	244 07/21/9	2 Roy	438	477		

FORM PTO-1449		IT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-2 Cont		APPLICATION NO. 10/672,961	
	FORMATION DISCLO		APPLICANT Glenn J. Le		CONFIRMATION NO. 9439	
<u>.</u>	OTATEMENT BY ALL ELOAN		FILING DAT September		GROUP 2811	
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5,151,	775 09/29/92	Hadwin	357	80		
5,156,	909 10/20/92	Henager, Jr. et al.	428	334		
5,203,	731 04/20/93	Zimmerman	445	24		
5,225,	771 07/06/93	Leedy	324	158		
5,236,	118 08/17/93	Bower et al.	228	193		
5,262,	351 11/16/93	Bureau et al.	437	183		
5,270,	261 12/14/93	Bertin et al.	437	209		
5,273,	940 12/28/93	Sanders	437	209		
5,274,	270 12/28/93	Tuckerman	257	758		
5,279,	865 01/18/94	Chebi et al.	427	574		
5,284,	796 02/08/94	Nakanishi et al.	437	183		
5,323,	035 06/21/94	Leedy	257	48		
5,324,	687 06/28/94	Wojnarowski	437	225		
5,354,	695 10/11/94	Leedy	438	411		
5,363,	021 11/08/94	MacDonald	315	366	•	
5,385,	909 01/31/95	Nelson et al.	514	291		
5,385,	632 01/31/95	Goossen	156	630		
5,420,	458 05/30/95	Shimoji	257	622		
5,424,	920 06/13/95	Miyake	361	735		
5,426,	072 06/20/95	Finnila	437	208		
5,426,	363 06/20/95	Akagi et al.	324	239		
5,432,	444 07/11/95	Yasohama et al.	324	240		
5,432,		Carson et al.	365	63		
5,434,			324	67		
5,451,			430	313		
5,453,			437	203		
5,457,			29	895		
5,476,			437	132		
5,489,			437	208		
5,502,			365	51		
5,512,			430	30		
5,527,			430	5		

FORM PTO-1449		NT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-2 Cont		APPLICATION NO. 10/672,961
	IFORMATION DISCL TATEMENT BY APPI		APPLICANT Glenn J. Lee		CONFIRMATION NO. 9439
S	OTAT ENGLAST OF A STATE OF			FILING DATE GROUP September 26, 2003 2811	
5,529,	829 06/25/96	Koskenmaki et al.	428	167	
5,534,		Frye et al.	437	209	
5,555,		Toshiaki et al.	365	200	
5,563,		Ramm et al.	437	51	
5,571,	741 11/05/96	Leedy	437	51	
5,580,		Leedy	430	5	
5,581,	498 12/03/96	Ludwig et al.	365	63	
5,582,	939 12/10/96	S Pierrat	430	5	
5,583,	688 12/10/96	6 Hornbeck	359	291	
5,592,	007 01/07/97	Leedy	257	347	
5,592,	01/07/97	Leedy	257	619	
5,595,	933 01/21/97	' Heijboer	439	20	
5,606,	186 02/25/97	' Noda	257	226	
5,627,	112 05/06/97	Tennant et al.	438	113	
5,629,	137 05/13/97	Leedy	430	313	
5,633,	209 05/27/97	Leedy	435	228	
5,637,	536 06/10/97	' Val	438	686	
5,654,	127 08/05/97	Leedy	430	315	
5,654,	220 08/05/97	Leedy	438	25	
5,656,	552 08/12/97	Hudak et al.	438	15	
5,675,	185 10/07/97	Chen et al.	257	774	
5,694,	588 12/02/97	Ohara et al.	395	566	
5,725,	995 03/10/98	B Leedy	430	315	
5,750,	211 05/12/98	Weise et al.	427	579	
5,760	478 06/02/98	Bozso et al.	257	777	
5,773	152 06/30/98	3 Okonogi	428	446	
5,786	116 07/28/98	Rolfson	430	5	
5,793	115 08/11/98	Zavracky et al.	257	777	
5,831,	280 11/03/98	Ray	257	48	
5,834	334 11/10/98	B Leedy	438	107	
5,840	593 11/24/98	B Leedy	438	6	
5,856	695 01/05/99	Ito et al.	257	370	

FORM PTO-	FORM PTO-1449 U.S. DEPART PATENT AND						ATTY. DOCKET NO. APPLICATION 10/672,961		ON NO.
	INFORMATIO			OSURE			APPLICANT Glenn J. Leedy		TION NO.
	STATEMEN <sup>-</sup>	I BY AP	PLIC	ANT				GROUP 2811	
	5,868,949	02/09/	99	Sotokaw	a et al.	216	18		
	5,869,354	02/09/	99	Leedy		438	110		
	5,870,176	02/09/		Sweatt e	et al.	355	53		
	5,880,010	03/09/		Davidso		438	455		
	5,882,532	03/16/	99	Field et a		216	2		
	5,902,118	05/11/	99	Hübner		438	106		
	5,915,167	06/22/		Leedy		438	108		
- "	5,946,559 08/31			Leedy		438	157		
	5,985,693	11/16/9				438	107		
	5,998,069	12/07/	99			430	5		
	6,008,126	12/28/	99			438	667		
	6,020,257	02/01/	00	Leedy	438		626		
	6,045,625	04/04/	00	Houston		148	33.3		
	6,084,284	07/04/	00	Adamic,	Jr.	257	506		
	6,097,096	08/01/	00	Gardner	et al.	257	777		
	6,133,640	10/17/	00	Leedy		257	778		
	6,194,245 B1	02/27/	01	Tayanak	<u></u> а	438	57		
	6,197,456 B1	03/06/	01	Aleshin e		430	5		
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